

Abstracts

Enhancement-Mode Pseudomorphic Inverted HEMT for Low Noise Amplifier (1991 Vol. II [MWSYM])

K. Ohmuro, H.I. Fujishiro, M. Itoh, H. Nakamura and S. Nishi. "Enhancement-Mode Pseudomorphic Inverted HEMT for Low Noise Amplifier (1991 Vol. II [MWSYM])." 1991 MTT-S International Microwave Symposium Digest 91.2 (1991 Vol. II [MWSYM]): 709-712.

The noise characteristics of pseudomorphic inverted HEMT (P-I-HEMT) were reported for the first time in this paper. The P-I-HEMTs were fabricated in enhancement-mode. Compared with pseudomorphic HEMT, P-I-HEMT shows a lower noise figure, especially at small drain voltage and small drain current. It was concluded that the P-I-HEMT structure is suitable for fine gate low noise FETs.

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